

L Number	Hits	Search Text	DB	Time stamp
1	129450	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)	USPAT; US-PGPUB	2004/06/05 21:16
2	75700	((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)	USPAT; US-PGPUB	2004/06/05 20:30
4	42247	((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)) and crystal\$10	USPAT; US-PGPUB	2004/06/05 20:31
5	41759	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)) and crystal\$10) and ((dop\$3 implant\$3) near50 (boron arsenic phosphorus) near50 crystal\$10 near50 (source and drain))	USPAT; US-PGPUB	2004/06/05 20:34
6	135	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)) and crystal\$10) and ((dop\$3 implant\$3) with (boron arsenic phosphorus) with crystal\$10 near50 (source and drain))	USPAT; US-PGPUB	2004/06/05 20:35
7	134	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)) and crystal\$10) and ((dop\$3 implant\$3) with (boron arsenic phosphorus) with crystal\$10) near50 (source and drain))	USPAT; US-PGPUB	2004/06/05 20:37
8	132	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)) and crystal\$10) and ((dop\$3 implant\$3) with (boron arsenic phosphorus) with crystal\$10) near50 (source and drain)) and (indium germanium silicon argon)	USPAT; US-PGPUB	2004/06/05 20:38
9	103	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and (anneal\$3 heat\$3)) and crystal\$10) and ((dop\$3 implant\$3) with (boron arsenic phosphorus) with crystal\$10) near50 (source and drain)) and (indium germanium silicon argon) and amorph\$8	USPAT; US-PGPUB	2004/06/05 21:22
10	1857	(anneal\$3 heat\$3) near10 after near10 amorph\$8	USPAT; US-PGPUB	2004/06/05 20:55
12	30	((anneal\$3 heat\$3) near10 after near10 amorph\$8) and ((implant\$3 dop\$4) near10 (boron arsenic phosphorus) near10 after near10 (anneal\$4 heat\$3))	USPAT; US-PGPUB	2004/06/05 21:16
13	74744	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/05 21:16

14	4161	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and amorph\$8	EPO; JPO; DERWENT; IBM_TDB	2004/06/05 21:16
15	14	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P) ) and amorph\$8 and ((implant\$3 dop\$4) near10 (boron arsenic phosphorus) near10 after near10 (anneal\$4 heat\$3))	EPO; JPO; DERWENT; IBM_TDB	2004/06/05 21:19
16	747	substrate near3 ((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.y"))	EPO; JPO; DERWENT; IBM_TDB	2004/06/05 21:27
17	2621	substrate near3 ((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.y"))	USPAT; US-PGPUB	2004/06/05 21:21
18	827	(substrate near3 ((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.y"))) and strain\$3	USPAT; US-PGPUB	2004/06/05 21:29
19	439	((substrate near3 ((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.y")))) and strain\$3 and (source and drain)	USPAT; US-PGPUB	2004/06/05 21:28
20	261	((substrate near3 ((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.y")))) and strain\$3 and (source and drain)) and amorph\$8	USPAT; US-PGPUB	2004/06/05 21:29
21	648	((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.x")) adj5 substrate	EPO; JPO; DERWENT; IBM_TDB	2004/06/05 21:28
23	1727	((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.x")) adj5 substrate	USPAT; US-PGPUB	2004/06/05 21:28
24	761	((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.x")) adj5 substrate) and (source and drain)	USPAT; US-PGPUB	2004/06/05 21:35
25	306	((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.x")) adj5 substrate) and (source and drain)) and amorph\$8	USPAT; US-PGPUB	2004/06/05 21:29
26	114	((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.x")) adj5 substrate) and (source and drain)) and amorph\$8 and strain\$3	USPAT; US-PGPUB	2004/06/05 21:29
28	54	((silicon near3 germanium) SiGe ("Si.sub.x" near2 "Ge.sub.x")) adj5 substrate) and (source and drain)	EPO; JPO; DERWENT; IBM_TDB	2004/06/05 21:36
-	128651	(implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")	USPAT; US-PGPUB	2004/06/05 20:30
-	128642	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)	USPAT; US-PGPUB	2004/06/05 20:29
-	50588	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate	USPAT; US-PGPUB	2004/05/20 20:45
-	46854	((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer)	USPAT; US-PGPUB	2004/05/20 20:40

-	48079	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor))	USPAT; US-PGPUB	2004/05/20 20:45
-	14167	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8	USPAT; US-PGPUB	2004/05/20 20:46
-	11531	(((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8) and (source and drain)	USPAT; US-PGPUB	2004/05/20 20:46
-	3578	((((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8) and (source and drain)) and (dose concentration)	USPAT; US-PGPUB	2004/05/20 20:42
-	3280	((((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8) and (source and drain)) and (dose concentration) and (anneal\$3 heat\$3)	USPAT; US-PGPUB	2004/05/20 20:43
-	2415	((((((implant\$3 dop\$4) near20 (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8) and (source and drain)) and (dose concentration) and (anneal\$3 heat\$3)) and diffus\$3	USPAT; US-PGPUB	2004/05/20 20:44
-	92315	(implant\$3 dop\$4) and (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2"))	EPO; JPO; DERWENT; IBM_TDB	2004/05/20 20:45
-	90266	((implant\$3 dop\$4) and (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)	EPO; JPO; DERWENT; IBM_TDB	2004/05/20 20:45
-	21247	((implant\$3 dop\$4) and (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate	EPO; JPO; DERWENT; IBM_TDB	2004/05/20 20:45
-	19862	((implant\$3 dop\$4) and (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)	EPO; JPO; DERWENT; IBM_TDB	2004/05/20 20:45
-	1543	(((((implant\$3 dop\$4) and (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helim He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8	EPO; JPO; DERWENT; IBM_TDB	2004/05/20 20:46

-	939	((((((implant\$3 dop\$4) and (germanium Ge silicon Si xenon Xe krypton Kr argon Ar helium He indium In neon Ne nitrogen N2 "N.sub.2")) and (arsenic As boron Br phosphorus P)) and gate) and (substrate wafer semiconductor)) and amorph\$8) and (source and drain)	EPO; JPO; DERWENT; IBM_TDB	2004/05/20 20:46
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